

# **IVMC 91**

## **Technical Digest**

**The Fourth International  
Vacuum Microelectronics Conference**

**August 22-24, 1991  
Nagahama, Japan**

**FOURTH INTERNATIONAL**



**CONFERENCE**

**Editors**

**S. Namba, Y. Nannichi, T. Utsumi**

**Organizing Committee of the Fourth International Vacuum Microelectronics Conference**

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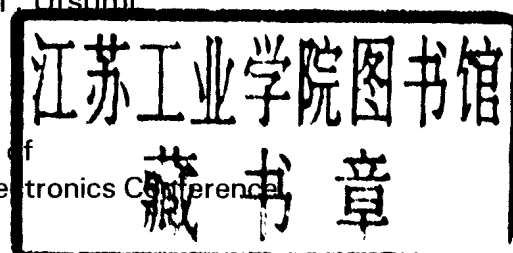
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**Sponsored by**

Organizing Committee of  
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## ***PREFACE***

On behalf of the local committee, we welcome all of you to the Fourth International Vacuum Microelectronics Conference (IVMC 91) to be held in Nagahama, Japan from the 22nd to the 24th, August 1991.

This digest contains extended abstracts to be presented at IVMC 91. A total of well over one hundred papers were submitted and among them 84 papers were accepted for presentation. This includes 9 invited talks, 38 oral presentations and 37 poster presentations. The last minute news, which we expect will keep arriving until the day of registration, are not included. The fact that the numbers of submitted papers have significantly increased over all previous conferences have shown the definite trend of rapidly growing interest and effort in this fascinating new field of technology all over the world. If the conference enhances our feeling that we are all comrades in making Vacuum Microelectronics a reality to open up a new frontier of science and technology and that we will be able to achieve our goals in a long run, then this conference is a great success.

We wish to express our sincere thanks to all attendees to the conference, especially to contributors who have done a tremendous job to present their works of excellence and to all attendees who are to do a superb job by participating in lively discussions during the conference.

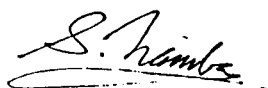
We also wish to express our warm gratitude to the local organizing committee members for spending considerable time and effort for organizing the conference and the dedicated staff of the Secretariat of the Business Center for Academic Societies in Japan for arranging the conference.

We also wish to express our sincere gratitude to Dr. H. F. Gray of Naval Research Laboratories who assisted tremendously our local committee to organize the conference and accepted to become a guest editor of the special issue of Vacuum Microelectronics in the Journal of Vacuum Science and Technology (B) to publish the full papers of this conference.

Finally this conference could never have been realized at this level without generous financial support from the public as well as private organizations in Japan whose names are listed on page v.

We hope that all of you enjoy your stay in Nagahama and its vicinity famous for its natural beauty and its unique history in one of the most dramatic periods of Japan.

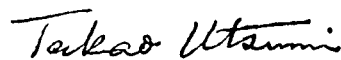
August 1991



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# CONTENTS

|                           |     |
|---------------------------|-----|
| <b>Preface</b> .....      | i   |
| <b>Organization</b> ..... | iii |

## Opening Session

Chairperson : Y. Nannichi (Univ. of Tsukuba, Japan)

### **Opening Address**

*S. Namba (Osaka Univ., Japan)*

### **Keynote Speeches**

|                                                                                                                                                   |   |
|---------------------------------------------------------------------------------------------------------------------------------------------------|---|
| <b>K-1 ☆☆ Coherence properties of a Field-Emitted Electron Beam and Its Application</b><br>A. Tonomura (Advanced Res. Lab., Hitachi, Japan) ..... | 2 |
| <b>K-2 ☆☆ Recent Development on "Microtips" Display at LETI</b><br>R. Meyer (LETI - CENG, France) .....                                           | 6 |

## Session I : Fundamental Issues

Chairpersons : V. Makhov (Zelenograd Res. Inst., U. S. S. R.)

M. Tsukada (Univ. of Tokyo, Japan)

|                                                                                                                                                                                          |    |
|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----|
| <b>I-1 ☆ Theory of Electron Emission in High Fields from Atomically Sharp Emitters</b><br>P. H. Cutler (Pennsylvania State Univ., U. S. A.) .....                                        | 12 |
| <b>I-2 Critical Features of the Field Emission Processes</b><br>G. N. Fursey (Leningrad Electric. Eng. Inst., U. S. S. R.) .....                                                         | 16 |
| <b>I-3 The Numerical Simulation of Electron Emission from Field Emitters Using the Wigner Distribution Approach</b><br>K. L. Jensen, A. K. Ganguly (Naval Res. Lab., U. S. A.) .....     | 18 |
| <b>I-4 Is There Image Potential Barrier Lowering for Field Emission ?</b><br>N. A. Cade (GEC-Marconi Ltd., U. K.) .....                                                                  | 20 |
| <b>I-5 Mechanism of Ion Desorption from a Negatively Biased Surface</b><br>M. Tsukada*, M. Sawamura**, M. Aono**, *** (*Univ. of Tokyo, **Aono Atomcraft Project, ***RIKEN, Japan) ..... | 22 |

## Session II : Field Emitter Arrays - 1

Chairpersons : C. P. Spindt (SRI International, U. S. A.)

J. Itoh (Electrotechnical Lab., Japan)

|                                                                                                                                                     |    |
|-----------------------------------------------------------------------------------------------------------------------------------------------------|----|
| <b>II-1 ☆ Fabrication and Characteristics of Si Field Emitter Arrays</b><br>K. Betsui (Fujitsu, Japan) .....                                        | 26 |
| <b>II-2 High Current Density Silicon FEAs</b><br>H. F. Gray, J. L. Shieh, G. W. Jones*, C. T. Sune* (Naval Res. Lab., *MCNC Center, U. S. A.) ..... | 30 |

☆☆ Keynote Speech

☆ Invited Talk

|             |                                                                                                                                                                                          |           |
|-------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----------|
| <b>II-3</b> | <b>Characterization and Fabrication of Single-Tip Field Emission Diodes Incorporating a Hemispherical Collector Electrode</b><br>D. Stephani, D. W. Branston (Siemens AG, Germany) ..... | <b>32</b> |
| <b>II-4</b> | <b>Fabrication of Silicon Point, Wedge, and Trench FEASs</b><br>G. W. Jones, C. T. Sune, H. F. Gray* (MCNC Center, *Naval Res. Lab., U. S. A.) .....                                     | <b>34</b> |
| <b>II-5</b> | <b>Field Electron Emission from Semiconductors</b><br>L. M. Baskin, G. N. Fursey (Leningrad Electric. Eng. Inst., U. S. S. R.) .....                                                     | <b>36</b> |

### **Session III : Field Emitter Arrays – 2**

Chairpersons : H. F. Gray (Naval Res. Lab., U. S. A.)

H. Tsuji (Kyoto Univ., Japan)

|                |                                                                                                                                                                                                     |           |
|----------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----------|
| <b>III-1 ☆</b> | <b>Field Emission Cathode Technology and Its Application</b><br>V. I. Makhov (Zelenograd Res. Inst., U. S. S. R.) .....                                                                             | <b>40</b> |
| <b>III-2</b>   | <b>The Effects of Size and Shape on Field-Emitter Array Performance</b><br>C. A. Spindt, C. E. Holland, A. Rosengreen, I. Brodie (SRI International, U. S. A.) .....                                | <b>44</b> |
| <b>III-3</b>   | <b>Metal-Film-Edge Field Emitter Array with a Self-aligned Gate</b><br>J. Itoh, S. Kanemaru, N. Nishimura*, K. Tsuburaya*, T. Watanabe*, S. Itoh*<br>(Electrotechnical Lab., * Futaba, Japan) ..... | <b>46</b> |
| <b>III-4</b>   | <b>Fabrication and Characteristics of Vacuum Microelectronic Devices with a Lateral Field Electron Emission Cathode</b><br>H. Komatsu (Seiko Epson, Japan) .....                                    | <b>48</b> |
| <b>III-5</b>   | <b>Field Emitter Array with Lateral Wedges</b><br>A. Kaneko, T. Kanno, K. Morishita (Matsushita, Japan) .....                                                                                       | <b>50</b> |

### **Session IV : Flat Display Panel**

Chairpersons : R. Meyer (LETI-CENG, France)

A. Kaneko (Matsushita, Japan)

|             |                                                                                                                                                                                                                                                                         |           |
|-------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----------|
| <b>IV-1</b> | <b>MIM Emitter Arrays Applied to Vacuum Fluorescent Display</b><br>R. B. Lubsanov, G. A. Vorobyev, V. M. Gaponenko, S. A. Ghyngazov,<br>N.I. Koshinov, S. S. Kramor, P.E. Troyan (Tomsk Inst.of Automatic Control Systems<br>and Radioelectronics, U. S. S. R.) .....   | <b>54</b> |
| <b>IV-2</b> | <b>Characteristics of Field Emitter Arrays for Light Source</b><br>Y. Kondo, J. Matsuura, H. Kimura (Matsushita, Japan) .....                                                                                                                                           | <b>56</b> |
| <b>IV-3</b> | <b>Investigation of a Cathodoluminescent Display Device with FE Cathodes</b><br>S. Itoh, T. Watanabe, T. Yamaura, K. Ohtsu, M. Yokoyama, M. Taniguchi,<br>H. Nakata, M. Miyamori, M. Yamaguchi, J. Itoh*, S. Kanemaru* (Futaba,<br>*Electrotechnical Lab., Japan) ..... | <b>58</b> |
| <b>IV-4</b> | <b>Field-Emission Array Cathodes for a Flat-Panel Display</b><br>N. N. Chubun, B. Ch. Djubua, B. I. Gorfinkel*, E. V. Rusina* (Istok R & P Corp,<br>*Volga Res. Inst., U. S. S. R.) .....                                                                               | <b>60</b> |

## Session V : Microwave Generation and Amplification

Chairpersons : Yu. Gulyaev (Acad. Sci. Moscow, U. S. S. R.)

K. Yokoo (Tohoku Univ., Japan)

|                                                                                                                                                                  |           |
|------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----------|
| <b>V-1 ☆ Recent Progress on Microwave Generation and Amplification by FEAS and other Microvacuum Devices</b>                                                     |           |
| <b>N. I. Sinitsyn (Acad. Sci. Moscow, U. S. S. R.)</b>                                                                                                           | <b>64</b> |
| <b>V-2 ☆ Field Emitter Structures in Microwave Generation and Amplification</b>                                                                                  |           |
| <b>N. E. McGruer (Northeastern Univ., U. S. A.)</b>                                                                                                              | <b>68</b> |
| <b>V-3 Investigation of Field-Emission Triodes at NRL</b>                                                                                                        |           |
| <b>P. M. Phillips, E. G. Zaidman, R. E. Neidert, C. Hor, C. A. Spindt* (Naval Res. Lab., *S. R. I. International, U. S. A.)</b>                                  | <b>72</b> |
| <b>V-4 High-Performance Heating Free Magnetron with Field Emission Excitation</b>                                                                                |           |
| <b>M. F. Kopylov, B. V. Bondarenko*, V. I. Makhov** (Special Design Bureau "Pluton", *Moscow Physical Technical Inst., **Zelenograd Res. Inst., U. S. S. R.)</b> | <b>74</b> |
| <b>V-5 Experimental Investigation of the Microvacuum Triode Amplifier</b>                                                                                        |           |
| <b>V. P. Sazonov, N. N. Chubun, B. Ch. Djubua, A. W. Galdetskiy, V. I. Bayle (Istok R &amp; P Corp. U. S. S. R.)</b>                                             | <b>76</b> |
| <b>V-6 Planar Field Emission Devices with Three-Dimensional Gate Structures</b>                                                                                  |           |
| <b>C. Nureki, M. Araragi (Yokogawa Electric., Japan)</b>                                                                                                         | <b>78</b> |

## Session VI : Fabrication

Chairpersons : J. Mitterauer (Tech. Univ. Wien, Austria)

M. Takai (Osaka Univ., Japan)

|                                                                                                                                                                                              |           |
|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----------|
| <b>VI-1 ☆ Applications of Masked Ion Beam Lithography to Vacuum Microelectronics</b>                                                                                                         |           |
| <b>J. C. Wolfe (Univ. of Houston, U. S. A.)</b>                                                                                                                                              | <b>82</b> |
| <b>VI-2 Fabrication of Silicon Cold-Cathodes by Electron Beam Evaporation</b>                                                                                                                |           |
| <b>M. Aslam, G. P. Myers, L. W. Cathey*, R. E. Elder*, B. E. Artz* (Michigan State Univ., *Ford Motor Co., U. S. A.)</b>                                                                     | <b>86</b> |
| <b>VI-3 Fabrication of Si Tips by Ar Ion Sputtering</b>                                                                                                                                      |           |
| <b>T. Asano, T. Tamon (Kyushu Inst. of Tech., Japan)</b>                                                                                                                                     | <b>88</b> |
| <b>VI-4 Ion Implantation and Low Energy Ion Mixing on a Field Emitter Surface</b>                                                                                                            |           |
| <b>A. L. Suvorov, V. A. Kuznetsov, A. F. Bobkov, R. Z. Bakhtizin, D. E. Dolin, T. V. Aladjikov, V. L. Ozhigov, A. F. Isakov (Inst. of Theoretical and Experimental Physics, U. S. S. R.)</b> | <b>90</b> |
| <b>VI-5 Vacuum Microelectronic Devices by Surface Micromachining</b>                                                                                                                         |           |
| <b>Q. Mei, S. Zurn, C. Ye, T. Tamagawa, R. J. Collins, D. L. Polla (Univ. of Minnesota, U. S. A.)</b>                                                                                        | <b>92</b> |

## Session VII : Properties and Characterization

Chairpersons : J. K. Wigmore (Univ. of Lancaster, U.K.)

H. Adachi (Muroran Inst. of Tech., Japan)

|                                                                                           |           |
|-------------------------------------------------------------------------------------------|-----------|
| <b>VII-1 ☆ Photofield and Energy-Resolved Field Emission Studies of Silicon Microtips</b> |           |
| <b>W. A. Phillips (GEC-Marconi Ltd, U. K.)</b>                                            | <b>96</b> |

|              |                                                                                                                                                                                                                                                                      |     |
|--------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|
| <b>VII-2</b> | Low-Frequency Fluctuations and Current Stability of Thin Film Field Emission Cathodes<br>R. Z. Bakhtizin, S. S. Ghots, N. N. Chubun*, B. Ch. Djubua* (Bashkir State Univ.,<br>R & P Corp "Istok", U. S. S. R.)                                                       | 100 |
| <b>VII-3</b> | Outgas from a Spindt Emitters Measured in an Extremely High Vacuum<br>C. Oshima, A. Ohtuka (Waseda Univ., Japan)                                                                                                                                                     | 102 |
| <b>VII-4</b> | Photoemission Determination of Work Functions and Surface Chemistry from Thin<br>Film Field Emitters<br>D. W. Nile, H. Hochst, G. W. Zajac*, J. O. Schreiner*, H. H. Busta*,<br>L. M. Eshelman** (Univ. of Wisconsin, *Amoco Tech. Co., **Purdue Univ.,<br>U. S. A.) | 104 |
| <b>VII-5</b> | Properties of the Tip Field Emitters, Covered by Superthin Insulating Films<br>V. G. Litovchenk, V. G. Popov, G. G. Kuleshova, A. F. Yatsenko, A. A. Evtuch<br>(Acad. of Sci. Ukrainian SSR, U. S. S. R.)                                                            | 106 |

### **Session VIII : Cold Emitters**

Chairpersons : P. H. Cutler (Pennsylvania State Univ., U. S. A.)  
S. Yamamoto (Hitachi, Japan)

|               |                                                                                                                                                                                                                              |     |
|---------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|
| <b>VIII-1</b> | Beam Deflection Concept for a Vacuum Microelectronic Microwave Amplifier<br>W. L. Ohlinger, R. K. Feeney, D. W. Hughes, H. M. Harris, D. N. Hill, L. R. Barnett*<br>(Georgia Inst. of Tech., *Mountain Technology, U. S. A.) | 110 |
| <b>VIII-2</b> | Electron Emission Properties of W-GaAs Schottky Electron Emission Diodes<br>T. Tsukamoto, N. Watanabe, M. Okunuki (Canon, Japan)                                                                                             | 112 |
| <b>VIII-3</b> | Thin-Film Cold Cathode Using Hot Electron in ZnS Layer<br>S. Okamoto, E. Nakazawa*, T. Suzuki (NHK Sci. & Tech. Res. Lab., *Kogakuin<br>Univ. Japan)                                                                         | 114 |
| <b>VIII-4</b> | Cold Cathode with SIS Tunnel Junction<br>T. Takami, K. Kojima, T. Noguchi*, K. Hamanaka<br>(Mitsubishi, *Nobeyama Radio Observatory, Japan)                                                                                  | 116 |
| <b>VIII-5</b> | Thin Film Emitter Development<br>S. Bandy, C. Nishimoto, R. LaRue, W. Anderson, G. Zdasiuk (Varian Res. Center,<br>U. S. A.)                                                                                                 | 118 |

### **Session IX : Novel Applications**

Chairpersons : D. W. Branston (Siemens AG, Germany)  
M. Okunuki (Canon, Japan)

|             |                                                                                                                                                                                       |     |
|-------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|
| <b>IX-1</b> | Low Voltage and Vacuum-free Field Emission Vacuum Microelectronic Tube<br>L. Enze (Xidian Univ., China)                                                                               | 122 |
| <b>IX-2</b> | Graphite Field Electron Array for Flat-panel Fluorescent Display<br>A. S. Kupryzashkin, V. A. Seliverstov, A. G. Shakhovskoy, E. P. Sheshin<br>(Moscow Phys. Tek. Inst., U. S. S. R.) | 124 |
| <b>IX-3</b> | Miniaturized Liquid Metal Ion Sources (MILMIS) for Space Applications<br>J. Mitterauer (Technische Universitat Wien, Austria)                                                         | 126 |
| <b>IX-4</b> | Microvacuum Diode Sensor for Measuring Displacement and Loads<br>J. C. Jiang, P. K. Allen, R. C. White (Columbia Univ., U. S. A.)                                                     | 128 |

|             |                                                                                                                                         |     |
|-------------|-----------------------------------------------------------------------------------------------------------------------------------------|-----|
| <b>IX-5</b> | <b>Distributed Amplifier Using FET and Secondary Emission</b><br>A. W. Galdetskiy, B. Ch. Djubua (Istok R & P Corp., U. S. S. R.) ..... | 130 |
|-------------|-----------------------------------------------------------------------------------------------------------------------------------------|-----|

## Session X : Poster Session

|              |                                                                                                                                                                                                                          |     |
|--------------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|
| <b>X-P1</b>  | (Withdrawn)                                                                                                                                                                                                              |     |
| <b>X-P2</b>  | <b>Tip Effect Interior Field Emission Mechanism of High Tc Superconductivity Materials</b><br>L. Enze (Xidian Univ., China) .....                                                                                        | 134 |
| <b>X-P3</b>  | <b>Field Emission through a Thin Oxide Layer</b><br>V. I. Makhov, V. A. Fedirko*, N. A. Duzhev, S. A. Kozmina*, (Zeleznograd Res. Inst. of Physical Problems, * "Microel" Res. Center, U. S. S. R.) .....                | 136 |
| <b>X-P4</b>  | <b>Surface State Enhanced Field Emission in Silicon</b><br>N. A. Cade, A. J. Miller, R. Johnston (GEC-Marconi Ltd., U. K.) .....                                                                                         | 138 |
| <b>X-P5</b>  | <b>Energy Distribution of Ions Bombarding Field Emitter Surface in High Vacuum</b><br>V. A. Kuznetsov, A. L. Suvorov (Inst. of Theoretical and Experimental Physics, U. S. S. R.) .....                                  | 140 |
| <b>X-P6</b>  | <b>Numerical Analysis of Spindt-type Cathode and Two Kind of Vacuum Microelectronics Devices</b><br>P. Mingzheng, N. Hanben (Academia Sinica, China) .....                                                               | 142 |
| <b>X-P7</b>  | <b>Fabrication and Characteristics of Tantalum Field Emitter Arrays</b><br>S. Fukuta, K. Betsui (Fujitsu, Japan) .....                                                                                                   | 144 |
| <b>X-P8</b>  | <b>Elimination of the "CROSS EFFECT" of Flat Panel Display by Matching Network Technology</b><br>Z. Renlin, P. Changxing (Xidian Univ., China) .....                                                                     | 146 |
| <b>X-P9</b>  | (Withdrawn)                                                                                                                                                                                                              |     |
| <b>X-P10</b> | <b>The Theory of Vacuum Microelectronic Distributed Microwave Devices (Amplifier, Multiplier, Oscillator)</b><br>M. V. Gavrilov, A. G. Rozhnev, D. V. Sokolov, D. I. Trubetskov (Saratov State Univ., U. S. S. R.) ..... | 148 |
| <b>X-P11</b> | <b>Theoretical Analysis of Lumped Microwave Amplifier with FEA Cathodes</b><br>A. W. Galdetskiy (Istok R & P Corp., U. S. S. R.) .....                                                                                   | 150 |
| <b>X-P12</b> | <b>Modelling and design of Vacuum Microelectronic Tubes</b><br>T. T. Tang, X. D. Liu (Xi'an Jiaotong Univ., China) .....                                                                                                 | 152 |
| <b>X-P13</b> | <b>Modeling of Static Triode Structures with Spindt-and Wedge-type Field Emitters</b><br>W. N. Carr, A. Q. Gui (New Jersey Inst. of Tech., U. S. A.) .....                                                               | 154 |
| <b>X-P14</b> | <b>The Analysis of the Field Emission Array Distributed Amplifier with Periodical Structure</b><br>V. A. Solntcev, V. V. Stepanchuk (Moscow Inst. of Electronic Machinery U. S. S. R.) .....                             | 156 |
| <b>X-P15</b> | <b>Lateral Triode with Metal-Film-Edge Field Emitter Array</b><br>J. Itoh, S. Kanemaru, N. Nishimura*, T. Watanabe*, S. Itoh* (Electrotechnical Lab., *Futaba Japan) .....                                               | 158 |
| <b>X-P16</b> | <b>Fabrication of Vacuum Microtriodes Using a "MOLD" Technique</b><br>G. Hashiguchi, H. Sakamoto, S. Kanazawa, K. Kawamura (Nippon Steel, Japan) .....                                                                   | 160 |

|              |                                                                                                                                                                                                                                                    |     |
|--------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|
| <b>X-P17</b> | Platinum Alloyed with a Metal of the II-nd Group of the Periodic System -<br>An Effective Source of Electron Emission<br>B. Ch. Djubua, V. N. Ilyin, O. K. Koultashev (R & P Corp. "Istok" , U. S. S. R.)                                          | 162 |
| <b>X-P18</b> | Electron Beam Assisted Fabrication of a Sharp Carbon Needle<br>H. Adachi, A. Abe, H. Nakane (Muroran Inst. of Technology, Japan)                                                                                                                   | 164 |
| <b>X-P19</b> | Cu Seed Cones as a Candidate for Field Electron Source of Vacuum Microelectronics<br>Devices<br>F. Okuyama, Y. Mori (Nagoya Inst. of Tech., Japan)                                                                                                 | 166 |
| <b>X-P20</b> | A Novel Fabrication Process for Planar Microelectronic Vacuum Devices<br>C. Y. Chen, D. P. Klemer, T. J. Shieh, J. L. Shieh, F. Younus (Univ. of Texas, U. S. A.)                                                                                  | 168 |
| <b>X-P21</b> | Planar Vacuum Diode Fabrication and Characterization<br>J. L. Shieh, C. Y. Chen, D. P. Klemer, T. J. Shieh (Univ. of Texas U. S. A.)                                                                                                               | 170 |
| <b>X-P22</b> | The Formation of Sub-0.1 Micron High Aspect Ratio Structures Using an Electron<br>Beam Contamination Technique<br>M. T. Browne, P. S. Charalambous, V. A. Kudryashov * (King's College London,<br>*Academy of Sciences Chernogolovka, U. S. S. R.) | 172 |
| <b>X-P23</b> | Fabrication Techniques for GaAs Schottky Electron Emission Diodes<br>N. Watanabe, T. Tsukamoto, Y. Okamura, M. Okunuki (Canon, Japan)                                                                                                              | 174 |
| <b>X-P24</b> | FEAT- A Field Emission Analysis Tool for Micro Vacuum Device Study<br>T. J. Shieh, F. Younus, D. P. Klemer, C. Y. Chen (Univ. of Texas, U. S. A.)                                                                                                  | 176 |
| <b>X-P25</b> | A Sub-micron Resolution UHV Probe Station for Characterization of Field Emitter<br>Arrays<br>J. L. Shieh, H. F. Gray (Naval Res. Lab., U. S. A.)                                                                                                   | 178 |
| <b>X-P26</b> | Effects of Emission Conditions on Burst Noise from Ti / W Thermal Field Emitters<br>K. Iwadate (NTT LSI Lab., Japan)                                                                                                                               | 180 |
| <b>X-P27</b> | DC and Microwave Characterization of Vacuum Microelectronics Devices<br>J. L. Shieh, R. Dehoyos, C. Y. Chen, D. P. Klemer, T. J. Shieh (Univ. of Texas,<br>U. S. A.)                                                                               | 182 |
| <b>X-P28</b> | Experimental Research for the Stability of Field Emission Current at the High Vacuum<br>M. Xianji, Z. Hao, (Xi'an Jiaotong Univ., China)                                                                                                           | 184 |
| <b>X-P29</b> | ESR of $\beta$ -SiC Formed by C Ion Implantation into Si Surface<br>N. Arai, T. Izumi, M. Deguchi*, A. Yoshida*, T. Hirao* (Tokai Univ. *Matsushita<br>Electric Ind., Co.,Ltd., Japan)                                                             | 186 |
| <b>X-P30</b> | Fluctuation Phenomena in Thin-films Formed Metal-Insulator-Metal<br>M. Khaskelberg, V. Davydov * (Pedagogical Inst., *Siberian Physico-Technical Inst.,<br>U. S. S. R.)                                                                            | 188 |
| <b>X-P31</b> | Life Time of Vacuum Microminiature Tubes with Hot Cathodes<br>B. I. Gorfinkel, Yu. V. Gulyaev, E. N. Petrov (Scientific Res. Inst. "Volga" ,<br>U. S. S. R.)                                                                                       | 190 |
| <b>X-P32</b> | A Study of Silicon Avalanche Cold Micro-Cathode<br>L. Qiong, X. Jingfang, T. Shihao, Yuan Meiying, X. Zheng, L. Chenglu*, Z. Duan**<br>(East China Normal Univ., *Sinica Academy Shanghai, **Shanghai Vacuum<br>Electrical Device Ltd, China)      | 192 |

|              |                                                                                                                                                                                                                        |     |
|--------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|
| <b>X-P33</b> | <b>Carbon Materials-Based Multitip Cathodes</b><br>Y. A. Grigoriev, V. C. Semeonov, V. I. Shestyorkin, Z. A. Yartseva (Res. &<br>Production Co. "ALMAZ" , U. S. S. R.) .....                                           | 194 |
| <b>X-P34</b> | <b>An Investigation on Overlayer-Substrate System : Cs on W (001)</b><br>C. Lu-Jun, *W. Ning, **W. Ding-Sheng, L. Enze (Xidian Univ., *Beijing Vacuum<br>Electronic Devices Res. Inst. **Academia Sinica, China) ..... | 196 |
| <b>X-P35</b> | <b>The Emission Properties of Formed MIM Structures</b><br>P. E. Troyan, G. A. Vorobyev, R. B. Lubsanov (Tomsk Inst. of Automatic<br>Control Systems and Radioelectronics, U. S. S. R.) .....                          | 198 |
| <b>X-P36</b> | <b>Field-Effect Controlled Vacuum Field-Emission Cathodes</b><br>A. C. Ting, C. M. Tang, T. A. Swyden*, D. McCarthy, M. C. Peckerar (Naval Res.<br>Lab., *FM Technologies Inc., U. S. A.) .....                        | 200 |
| <b>X-P37</b> | <b>Application of a Spindt Emitter to an Ionization Gauge for an Extremely High Vacuum</b><br>A. Otuka, M. Yoshino, C. Oshima (Waseda Univ., Japan) .....                                                              | 202 |
| <b>X-P38</b> | <b>Fabrication of a Tunnel Sensor with Cantilever Structure</b><br>T. Asano, R. Kajiwara (Kyushu Inst. of Tech., Japan) .....                                                                                          | 204 |

## **Closing Session**

Chairperson : J. Ishikawa (Kyoto Univ., Japan)

### ***Closing Remarks***

*H. F. Gray (Naval Res. Center, U. S. A.)*

*J. Mitterauer (Technische Univ. Wien, Austria)*

*T. Utsumi (Canon, Japan)*

# **Opening Session**

**Opening Address**

**Keynote Speeches**

## COHERENCE PROPERTIES OF A FIELD EMISSION ELECTRON BEAM AND ITS APPLICATIONS

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### 1. INTRODUCTION

An electron beam field emitted from a pointed tip has a higher brightness (current density per solid angle) and a narrower energy spread than a thermal emission beam.<sup>1)</sup> In 1968, these features were effectively employed for forming a fine probe and improving the resolution limit of scanning electron microscopes by Crewe.<sup>2)</sup> This beam was also used in 1978 for a "coherent" electron beam.<sup>3)</sup> Using this beam, the total number of electron interference fringes recordable on film increased from 300 to more than 3,000 with an exposure time of 30 seconds, and the fringes become directly observable on the fluorescent screen.

As a result of this improvement, electron holography became practical in that its reconstructed images are comparable in resolution to electron micrographs. New application fields for electron holog-

raphy are now being opened up. For example, flux lines penetrating a superconductor can be seen in the form of magnetic lines of force in interference micrographs.<sup>4)</sup> Their dynamics can also be observed.<sup>5)</sup>

### 2. ELECTRON GUN

An example of our field emission electron gun is schematically shown in Fig. 1. Electrons are emitted from a tungsten tip 1,000 Å in radius, and accelerated up to 125 kV through three-stage accelerating electrodes. Electrons are focused through condenser lenses to form a fine probe a few hundreds of Å in diameter, and illuminate a specimen.

The illumination angle can be made as small as  $5 \times 10^{-8}$  radians, allowing the spatial coherence length in the specimen plane to be as large as 80 μm. The spatial coherence length is the maximum diameter of the circular region within which the electron wavefront can be defined. Interference can occur within this region.

The time coherence length of an electron beam is given by  $\lambda (2E/\Delta E)$ . Here,  $\lambda$  is the electron wavelength,  $E$  is the kinetic electron energy, and  $\Delta E$  is the energy spread. When  $E=100$  keV and  $\Delta E=0.3$  eV, the time coherence length is around 2 μm. Interference occurs when the path difference between two beams is smaller than this length. This value seems extremely small when compared with that of a laser beam, but this is not the case. The number of wavelengths contained in this length is as large as 700,000. Usually electron interference experiments are not restricted by the time coherence length. There have been, however, two experiments in which this occurred.<sup>6,7)</sup>

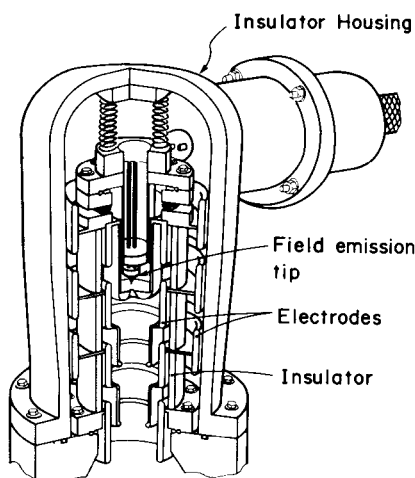


Fig. 1. Field emission electron gun.

### 3. ELECTRON HOLOGRAPHY

Electron holography<sup>8)</sup> is a two-step imaging method using electron and light waves (see Fig. 2). An electron wave illuminates an object and is then scattered. A reference wave that has been tilted by a prism is then projected onto the scattered wave to form an interference pattern, which is recorded on film. This film, called a hologram, is subsequently illuminated by a collimated laser beam. The exact image is then reproduced three-dimensionally.

In holography, two images are always reconstructed. They are exactly the same except that their amplitudes are complex conjugates of each other—that is, their phase values are reversed in sign. The conjugate image is a nuisance in image observations, but it plays an important role in high-precision phase measurements. Holography imaging is unique in that it requires no lenses and uses only the most fundamental wave properties of interference and diffraction. Therefore, imaging is possible even between completely different waves. A large wavelength difference is not a problem, since interference and diffraction always take place in wavelength units.

Once electron wavefronts are reproduced as light wavefronts, versatile optical techniques can be supplemented by electron optics. One example is a holographic interference microscope. In this case, an interference micrograph, or contour map of the wavefront, can be obtained simply by combining an optical

interferometer in the optical reconstruction stage. This is done by overlapping an optical plane wave with the reconstructed image. If a conjugate image instead of a plane wave overlaps this wavefront, the phase difference becomes twice as large, as if the phase distribution were amplified two times. By repeating this technique, a phase shift even as small as  $1/100$  of a wavelength can be detected.

Phase-amplified interference electron microscopy provides information about a specimen's thickness distribution in atomic dimensions<sup>9)</sup> and microscopic distribution of the electric<sup>10)</sup> and magnetic<sup>11)</sup> fields.

### 4. APPLICATIONS

#### a) Specimen thickness measurements:

An interference micrograph amplified 24 times of a cleaved molybdenite thin film is shown in Fig. 3. The phase distribution is displayed here as a deviation from regular fringes, i. e., an interferogram. Steps A, B, and C in the micrograph correspond to one, three, and five layers of atomic surface steps. The thickness change at step A is  $6.2 \text{ \AA}$  (one-half of the c-axis spacing), and produces a phase shift of  $2\pi/50$ . This experiment shows that a phase shift can be detected with an accuracy of the order of  $2\pi/100$ .

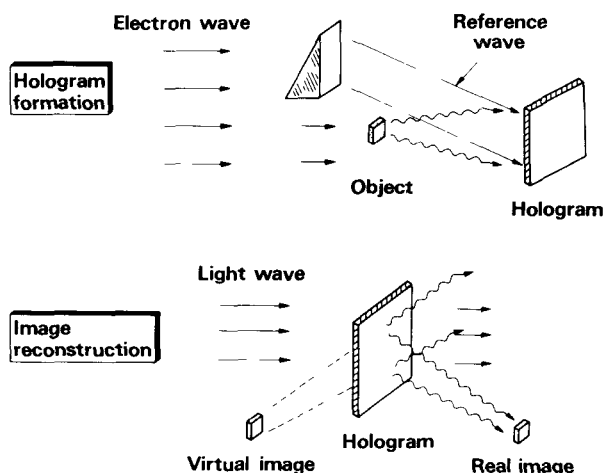


Fig. 2. Principle behind electron holography.

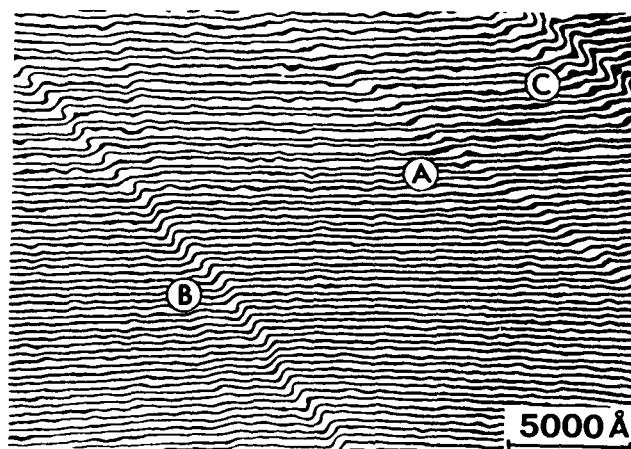


Fig. 3. Interferogram of molybdenite thin film (phase amplification:  $\times 24$ ).